**Product data sheet** 

## 1. General description

P-channel enhancement mode Field-Effect Transistor (FET) in a small SOT23 (TO-236AB) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

#### 2. Features and benefits

- Low threshold voltage
- Low on-state resistance
- Trench MOSFET technology

## 3. Applications

- Low power DC-to-DC converters
- Load switching
- Battery management
- · Battery powered portable equipment

### 4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-	-20	V
$V_{GS}$	gate-source voltage			-12	-	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>sp</sub> = 25 °C		-	-	-4.3	Α
Static characteristics							
R <sub>DSon</sub>	drain-source on-state resistance	$V_{GS}$ = -4.5 V; $I_D$ = -2.8 A; $T_j$ = 25 °C		-	58	74	mΩ



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## 5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	<u> </u>	D
2	S	source		
3	D	drain	1	G S S 017aaa257

## 6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PMV65XP	TO-236AB	plastic surface-mounted package; 3 leads	SOT23			

## 7. Marking

Table 4. Marking codes

Type number	Marking code [1]
PMV65XP	%M9

<sup>[1] % =</sup> placeholder for manufacturing site code

# 8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
$V_{DS}$	drain-source voltage	T <sub>j</sub> = 25 °C		-	-20	V
$V_{GS}$	gate-source voltage			-12	12	V
I <sub>D</sub>	drain current	V <sub>GS</sub> = -4.5 V; T <sub>sp</sub> = 25 °C		-	-4.3	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 25 °C	[1]	-	-2.8	Α
		V <sub>GS</sub> = -4.5 V; T <sub>amb</sub> = 100 °C	[1]	-	-1.8	Α
I <sub>DM</sub>	peak drain current	$T_{amb}$ = 25 °C; single pulse; $t_p \le 10$ μs		-	-16	Α
P <sub>tot</sub>	total power dissipation	T <sub>amb</sub> = 25 °C	<u>[2]</u>	-	480	mW
			[1]	-	833	mW
		$T_{sp} = 25  ^{\circ}C$		-	4165	mW

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Symbol	Parameter	Conditions		Min	Max	Unit	
Tj	junction temperature			-55	150	°C	
T <sub>amb</sub>	ambient temperature			-55	150	°C	
T <sub>stg</sub>	storage temperature			-65	150	°C	
Source-drain diode							
I <sub>S</sub>	source current	T <sub>sp</sub> = 25 °C		-	-1.6	Α	

- Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>. Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated and standard footprint.

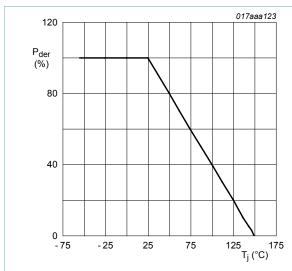


Fig. 1. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

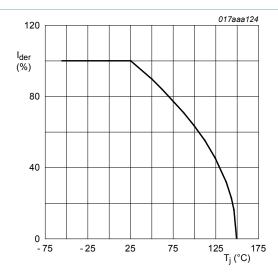


Fig. 2. Normalized continuous drain current as a function of junction temperature

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}\text{C})}} \times 100 \%$$

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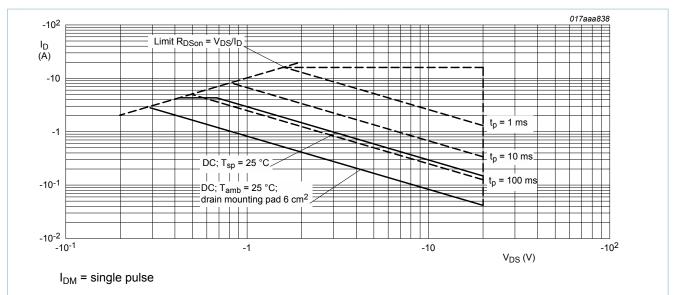


Fig. 3. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drain-source voltage

#### 9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient	in free air	[1]	-	230	260	K/W
			[2]	-	125	150	K/W
R <sub>th(j-sp)</sub>	thermal resistance from junction to solder point			-	25	30	K/W

- [1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 6 cm<sup>2</sup>.

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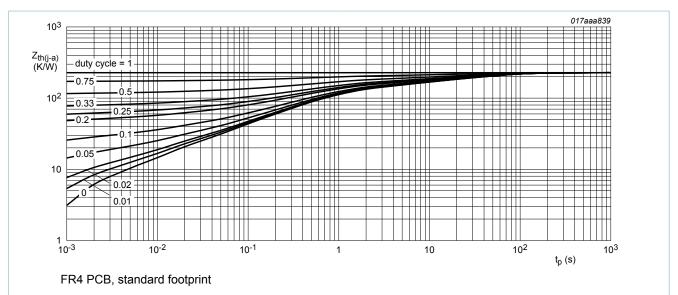


Fig. 4. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

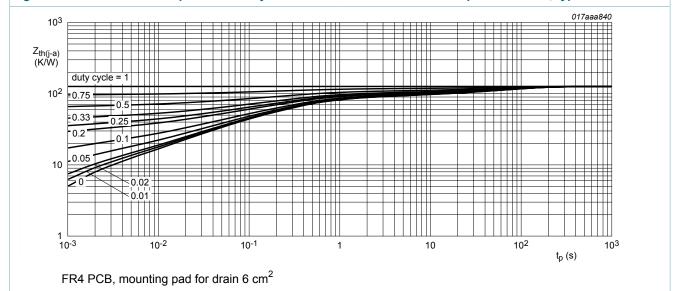


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

#### 10. Characteristics

Table 7. Characteristics

Cumbal	Darameter	Conditions		Min	Tren	May	Unit	
Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
Static characteristics								
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = -250 \mu A; V_{GS} = 0 V; T_j = 25 °C$		-20	-	-	V	
$V_{GSth}$	gate-source threshold voltage	$I_D$ = -250 $\mu$ A; $V_{DS}$ = $V_{GS}$ ; $T_j$ = 25 °C		-0.47	-0.65	-0.9	V	
I <sub>DSS</sub>	drain leakage current	$V_{DS}$ = -20 V; $V_{GS}$ = 0 V; $T_j$ = 25 °C		-	-	-1	μA	
		V <sub>DS</sub> = -20 V; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 150 °C		-	-	-100	μA	
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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
I <sub>GSS</sub>	gate leakage current	V <sub>GS</sub> = -12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	-100	nA
		V <sub>GS</sub> = 12 V; V <sub>DS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-	100	nA
R <sub>DSon</sub>	drain-source on-state	$V_{GS}$ = -4.5 V; $I_D$ = -2.8 A; $T_j$ = 25 °C	-	58	74	mΩ
	resistance	$V_{GS}$ = -4.5 V; $I_{D}$ = -2.8 A; $T_{j}$ = 150 °C	-	82	105	mΩ
		$V_{GS}$ = -2.5 V; $I_D$ = -2.3 A; $T_j$ = 25 °C	-	67	92	mΩ
		$V_{GS}$ = -1.8 V; $I_D$ = -1 A; $T_j$ = 25 °C	-	87	135	mΩ
9fs	forward transconductance	$V_{DS}$ = -10 V; $I_{D}$ = -2.8 A; $T_{j}$ = 25 °C	-	15	-	S
Dynamic cl	naracteristics		,			
Q <sub>G(tot)</sub>	total gate charge	$V_{DS}$ = -6 V; $I_{D}$ = -2.8 A; $V_{GS}$ = -4.5 V; $T_{j}$ = 25 °C	-	7.7	-	nC
Q <sub>GS</sub>	gate-source charge		-	1	-	nC
$Q_{GD}$	gate-drain charge		-	1.65	-	nC
C <sub>iss</sub>	input capacitance	$V_{DS}$ = -20 V; f = 1 MHz; $V_{GS}$ = 0 V;	-	744	-	pF
C <sub>oss</sub>	output capacitance	T <sub>j</sub> = 25 °C	-	65	-	pF
C <sub>rss</sub>	reverse transfer capacitance		-	53	-	pF
t <sub>d(on)</sub>	turn-on delay time	$V_{DS}$ = -6 V; $V_{GS}$ = -4.5 V; $R_{G(ext)}$ = 6 $\Omega$ ;	-	7	-	ns
t <sub>r</sub>	rise time	T <sub>j</sub> = 25 °C; I <sub>D</sub> = -1 A	-	18	-	ns
t <sub>d(off)</sub>	turn-off delay time		-	135	-	ns
t <sub>f</sub>	fall time		-	68	-	ns
Source-dra	in diode		I	1	1	
V <sub>SD</sub>	source-drain voltage	I <sub>S</sub> = -0.9 A; V <sub>GS</sub> = 0 V; T <sub>j</sub> = 25 °C	-	-0.8	-1.2	V

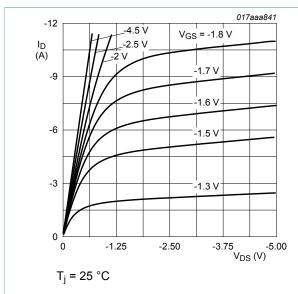


Fig. 6. Output characteristics: drain current as a function of drain-source voltage; typical values

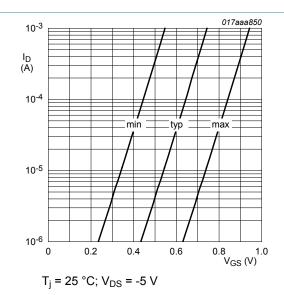


Fig. 7. Sub-threshold drain current as a function of gate-source voltage

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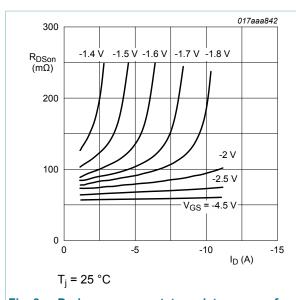


Fig. 8. Drain-source on-state resistance as a function of drain current; typical values

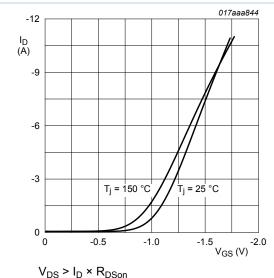


Fig. 10. Transfer characteristics: drain current as a function of gate-source voltage; typical values

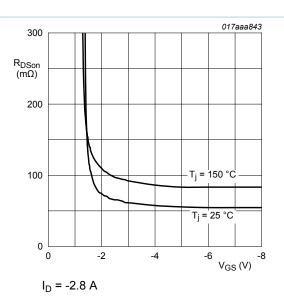


Fig. 9. Drain-source on-state resistance as a function of gate-source voltage; typical values

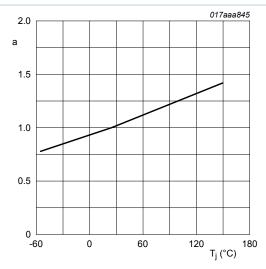


Fig. 11. Normalized drain-source on-state resistance as a function of junction temperature; typical values

$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$

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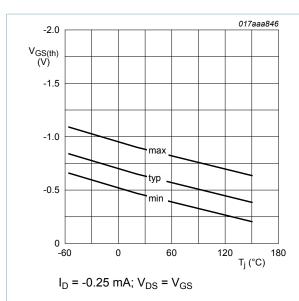


Fig. 12. Gate-source threshold voltage as a function of junction temperature

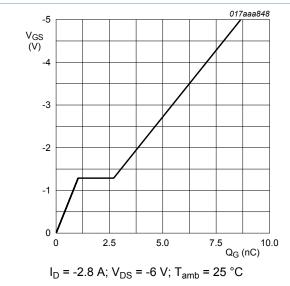


Fig. 14. Gate-source voltage as a function of gate charge; typical values

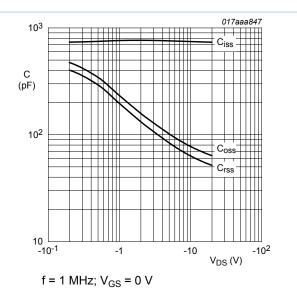


Fig. 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

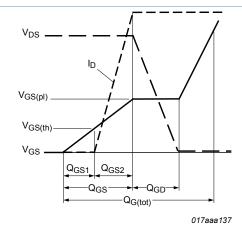
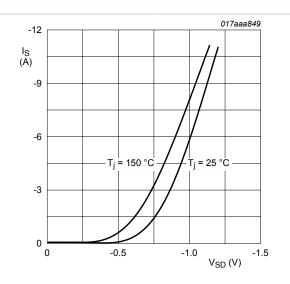


Fig. 15. Gate charge waveform definitions

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 $V_{GS} = 0 V$ 

(1) T<sub>j</sub> = 150 °C

(2)  $T_i = 25 \,^{\circ}\text{C}$ 

Fig. 16. Source current as a function of source-drain voltage; typical values

## 11. Test information

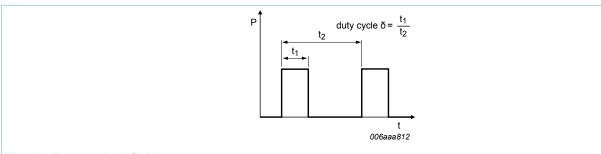
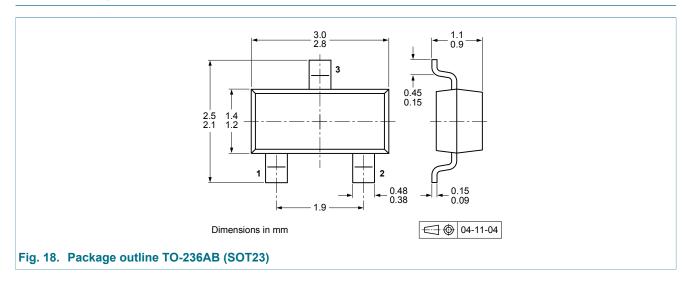


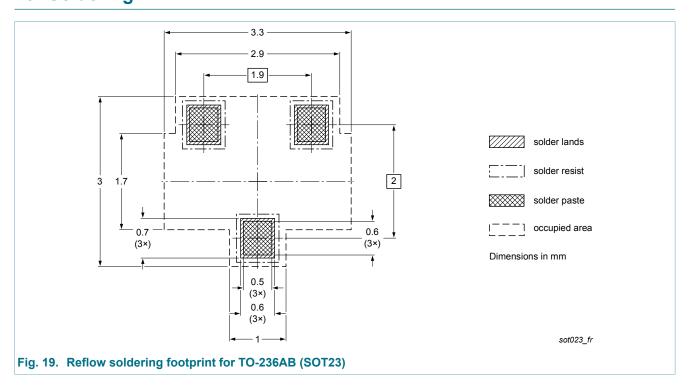
Fig. 17. Duty cycle definition

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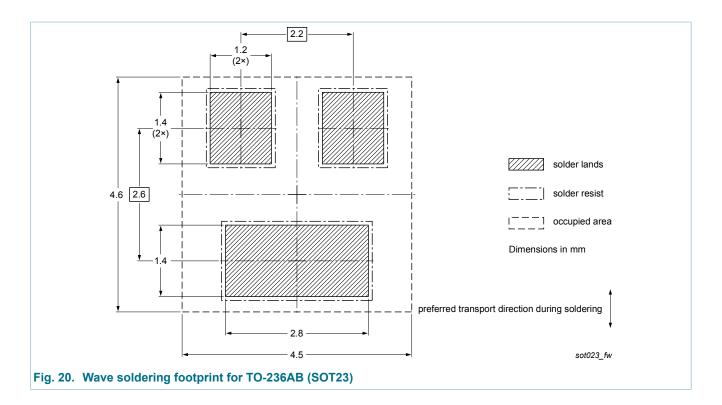
## 12. Package outline



## 13. Soldering



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## 14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes				
PMV65XP v.2	20130212	Product data sheet	-	PMV65XP v.1				
Modifications:	Pinning information	Pinning information corrected						
PMV65XP v.1	20120921	Product data sheet	-	-				

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#### 15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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